

VRS0; Q P RV

Gr xe0h Q0FKDQQH0 P RV IHW lq d VRS0; S0dvwlf Sdfnd j hl

$V_{DS}(V)=30V$ $I_D=16A$

$R_{DS(ON)}@10V<8m\Omega$ (Typ. 7.6mR)

$R_{DS(ON)}@4.5V<12m\Omega$ (Typ. 10.8mR)

HF Product.

P E2QE2X P SF2YJD

/ GF0GF /

Kl j k l uht xhqf | Srlqw0ri00rdg V|qfku r qrxv Exfn Frqyhuw hu i ru P E2QE2X P SF2YJD/

Qhwz runlq j GF0GF Sr z hu V|vw h p /0rdg Vz lwfk l

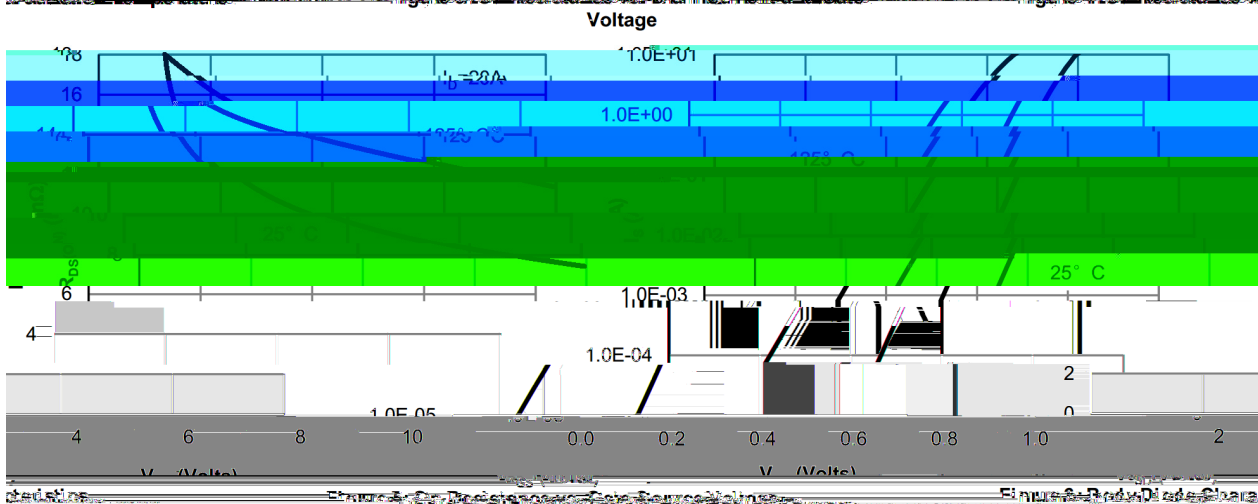
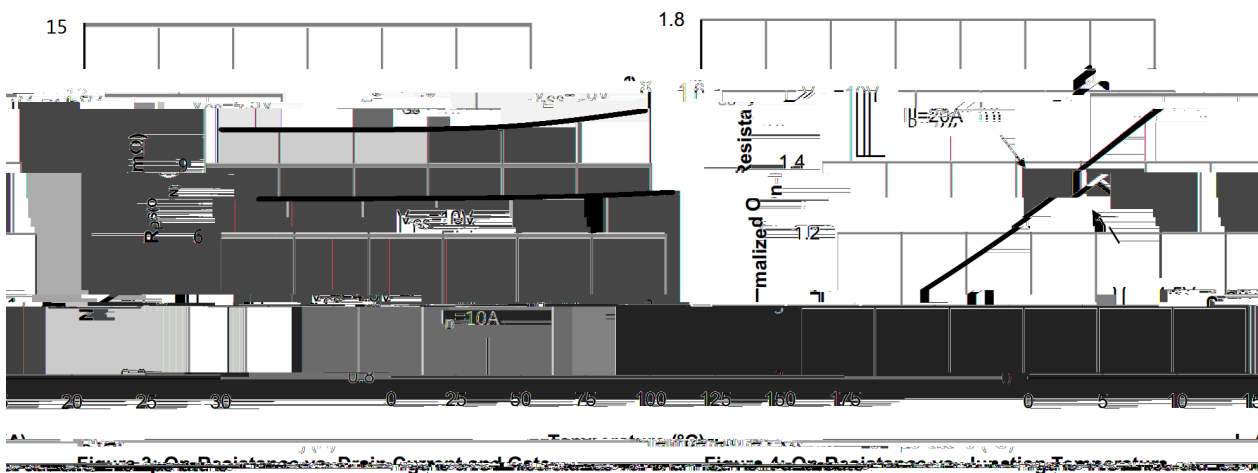
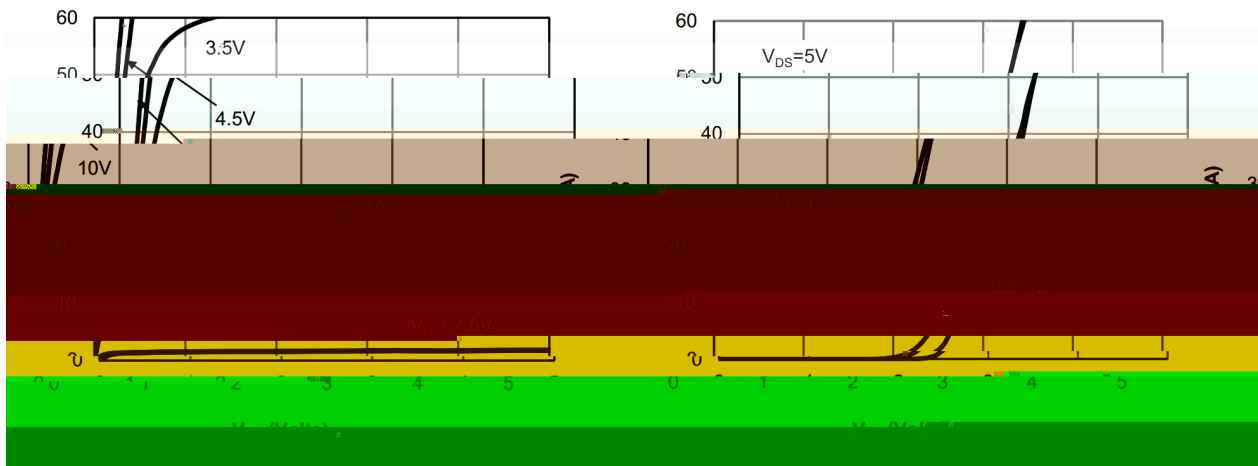
PIN1 S1 PIN 2 G1 PIN 3 S2 PIN 4 G2

PIN 5 D2 PIN 6 D2 PIN 7 D1 PIN 8 D1

See Marking Instructions.

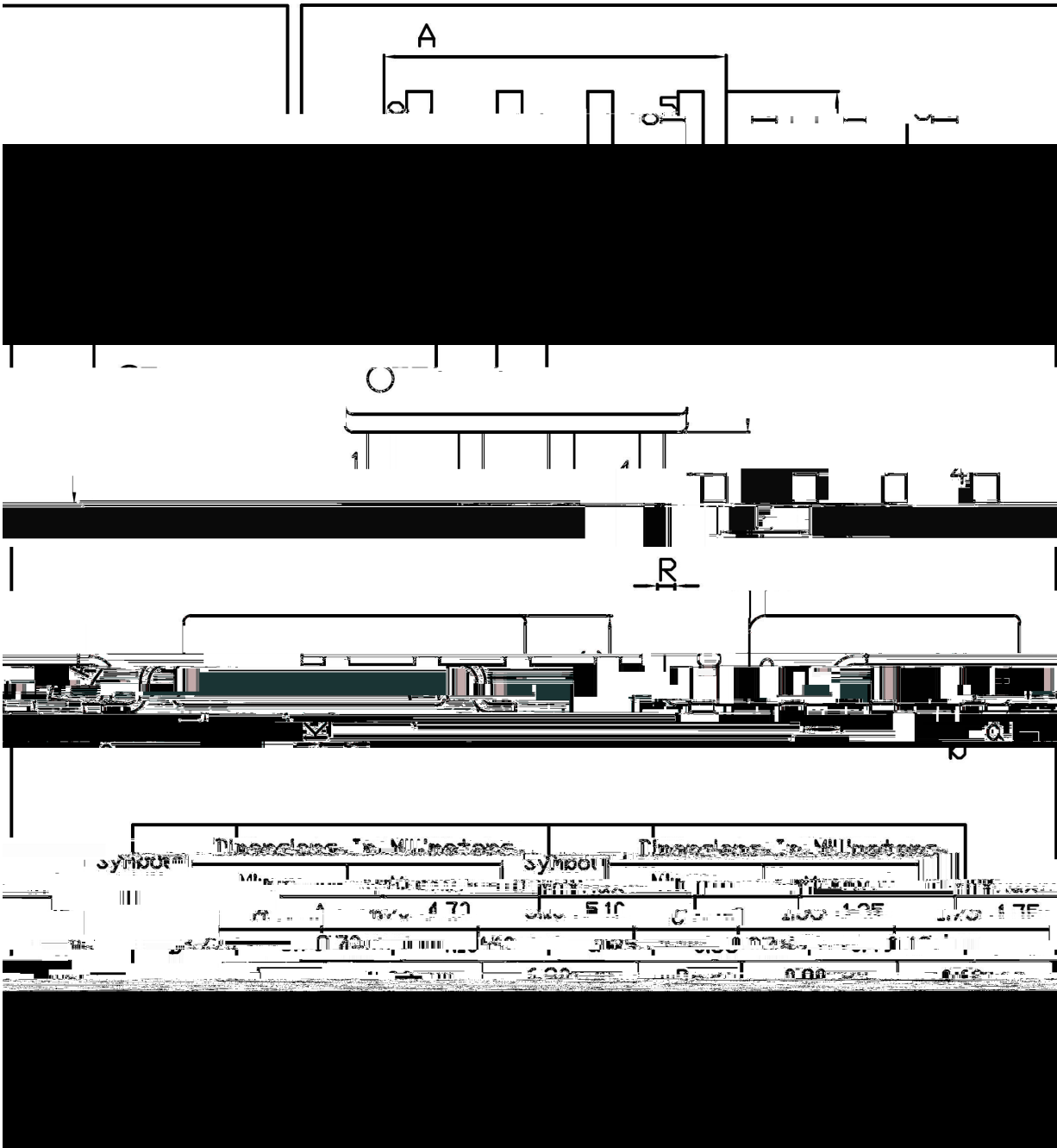
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	16	A
Pulsed Drain Current	I_{DM}	59	A
Power Dissipation	P_D	3.2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	
Maximum Junction-to-Ambient	$R_{\theta JA}(\text{Steady-State})$	39	/W

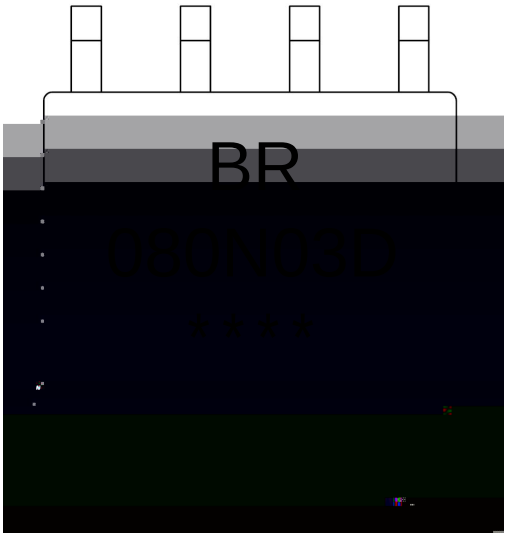
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7		



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SEP 0 10:11:11 AM '23





BR
080N03D

Note:
BR: Company Code
080N03D: Product Type
****: Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|--------------|-------------|---|
| 1 | 150 ~ 180℃ | 60 ~ 90sec; | 1.Preheating:150~180℃, Time:60~90sec. |
| 2 | 245 ± 5℃ | 5 ± 0.5sec; | 2.Peak Temp.:245 ± 5℃, Duration:5 ± 0.5sec. |
| 3 | 2 ~ 10℃/sec. | | 3. Cooling Speed: 2~10℃/sec. |

605 ± 5℃